

Appln. No. 10/798,547
Amdt. dated May 24, 2005
Reply to Office Action of February 9, 2005

PATENT

Amendments to the Abstract:

On page 27, please replace the Abstract with the following new abstract:

A non-volatile memory element is operated, in part, in two phases. During the first phase, a voltage is applied to a first node coupled to the nonvolatile memory element to generate an initial voltage. During the second phase, a voltage is coupled through at least one capacitor to charge pump the initial voltage to a level sufficient for programming or erasing the non-volatile memory element.